

Michael Graef

List of Publications by Year in descending order

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Version: 2024-02-01

16
papers

184
citations

1937685

4
h-index

2272923

4
g-index

16
all docs

16
docs citations

16
times ranked

164
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 1 | Advanced analytical modeling of double-gate Tunnel-FETs – A performance evaluation. Solid-State Electronics, 2018, 141, 31-39. | 1.4 | 9 |
| 2 | Static noise margin analysis of 8T TFET SRAM cells using a 2D compact model adapted to measurement data of fabricated TFET devices. , 2017, , . | | 2 |
| 3 | DC/AC Compact Modeling of TFETs for Circuit Simulation of Logic Cells Based on an Analytical Physics-Based Framework. , 2017, , . | | 0 |
| 4 | Comparative numerical analysis and analytical RDF-modeling of MOSFETs and DG Tunnel-FETs. , 2016, , . | | 3 |
| 5 | Numerical analysis and analytical modeling of RDF in DG Tunnel-FETs. , 2016, , . | | 4 |
| 6 | Modeling approach for rapid NEGF-based simulation of ballistic current in ultra-short DG MOSFETs. , 2016, , . | | 2 |
| 7 | Implementation of a DC compact model for double-gate Tunnel-FET based on 2D calculations and application in circuit simulation. , 2016, , . | | 8 |
| 8 | Analytical approach to consider Gaussian junction profiles in compact models of tunnel-FETs. , 2015, , . | | 3 |
| 9 | Wavelet-based calculation of the transmission coefficient for tunneling events in Tunnel-FETs. , 2015, , . | | 3 |
| 10 | Modeling and performance study of nanoscale double gate junctionless and inversion mode MOSFETs including carrier quantization effects. Microelectronics Journal, 2014, 45, 1220-1225. | 2.0 | 9 |
| 11 | Compact Model for Short-Channel Junctionless Accumulation Mode Double Gate MOSFETs. IEEE Transactions on Electron Devices, 2014, 61, 288-299. | 3.0 | 95 |
| 12 | Improved analytical potential modeling in double-gate tunnel-FETs. , 2014, , . | | 8 |
| 13 | Two-dimensional modeling of an ultra-thin body single-gate Si Tunnel-FET. , 2014, , . | | 6 |
| 14 | A 2D closed form model for the electrostatics in hetero-junction double-gate tunnel-FETs for calculation of band-to-band tunneling current. Microelectronics Journal, 2014, 45, 1144-1153. | 2.0 | 26 |
| 15 | Two-dimensional bias dependent model for the screening length in double-gate Tunnel-FETs. , 2013, , . | | 2 |
| 16 | Model for investigation of I_{on}/I_{off} ratios in short-channel junctionless double gate MOSFETs. , 2013, , . | | 4 |